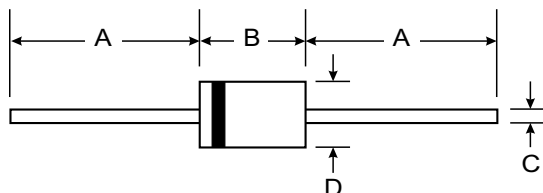


Features

- For general purpose applications
- These diodes features very low turn-on voltage and fast switching.
- These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- This diode is also available in the MiniMELF case with the type designation LI47.
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Mechanical Data

- Case: DO-35 glass case
- Polarity: Color band denotes cathodes end
- Weight: Approx. 0.13 gram

DO-35		
Dim	Min	Max
A	25.40	—
B	—	4.00
C	—	0.60
D	—	2.00
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

	Symbols	Value		Units
Repetitive Peak Reverse Voltage	V _{RRM}	20		V
Forward Continuous Current at T _A =25°C	I _F	350 ¹⁾		mA
Repetitive Peak Forward Current at t _p ≤1s, δ≤0.5 T _A =25°C	I _{FRM}	1 ¹⁾		A
Surge forward current at t _p ≤10ms, T _A =25°C	I _{FSM}	7.5 ¹⁾		A
Power Dissipation at T _A =65°C	P _{tot}	330 ¹⁾		mW
Junction temperature	T _J	125		°C
Ambient Operating temperature Range	T _A	-65 to +125		°C
Storage Temperature Range	T _{STG}	-65 to +150		°C
	Symbols	Min.	Typ.	Max.
Reverse breakdown voltage Tested with 10μA Pulses	V(BR) _R	20		
Forward voltage				
Pulse Test t _p ≤300μs, δ≤2%	V _F			0.25
at I _F =0.1mA	V _F			0.40
at I _F =10mA	V _F			1.0
at I _F =300mA	V _F			
Leakage current				
pulse test t _p ≤300μs, δ≤2%	I _R			4
at V _R =10V	I _R			20
at V _R =10V, T _J =60°C	I _R			10
at V _R =20V	I _R			30
at V _R =20V, T _J =60°C	I _R			
Capacitance at V _R =1V, f=1MHz	C _J		12	
Thermal resistance junction to ambient Air	R _{θJA}			300 ¹⁾

1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature(DO-35)